| Reg. No. | | | | | | | | | | | |
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Eighth Semester B.Tech. Degree Examination, November 2015 (2008 Scheme)

08.801 : NANOELECTRONICS (TA)

Time: 3 Hours

Max. Marks: 100

PART-A

Answer all questions. Each question carries 4 marks:

1. Mention three applications of nanotechnology.



- 2. What is self assembly?
- 3. Give the principle of photoluminescence spectroscopy.
- 4. Draw the bandstructures of npn homojunction and heterojunction transistors.
- 5. Compare SETs and MOSFETs.
- 6. Discuss the principle of stimulated emission.
- 7. What is microlaser? Explain its principle.
- 8. What are the possible energy levels in a quantum wire?
- 9. What is Bloch oscillation? Give an expression for the period of Bloch oscillation.
- 10. What is quantum Hall effect? What are its applications? (10×4=40 Marks)



PART-B

Answer any two questions from each Module. Each question carries 10 marks:

Module - I

- 11. Explain the limitations of conventional microelectronics in detail.
- 12. Explain any one chemical vapour deposition method.
- 13. With a suitable schematic, explain the operation of atomic force microscope.

Module - II

- 14. Explain the theory involved in integer quantum Hall effect.
- 15. Draw the density of states for a ID and OD electron system and explain.
- 16. Briefly discuss about modulation doped quantum and multiple quantum wells.

Module - III

- 17. Explain the principle of operation of MODFET and mention its few advantages.
- Explain in detail device structure and characteristics of resonant tunneling transistor.
- 19. Describe the working principle of heterojunction semiconductor laser.

(6×10=60 Marks)